



100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	Max R _{DS(on)}	Max I _D T _A = 25°C (Note 5)	
100V	250mΩ @ V _{GS} = 10V	1.9A	
	300mΩ @ V _{GS} = 6V	1.68A	

Description and Applications

This MOSFET features a unique structure, combining the benefits of low on-resistance and fast switching, making it ideal for high-efficiency, power management applications.

- DC DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

Features and Benefits

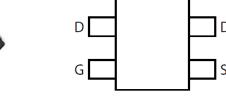
- Low On-Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

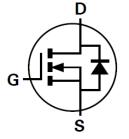
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208(2)
- Weight: 0.015 grams (Approximate)









Top View

Pinout Top-view

Device symbol

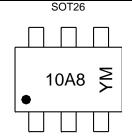
Ordering Information (Note 4)

Part Number	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMN10A08E6TA	7	8	3000
ZXMN10A08E6TC	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



10A8 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	201	5	2016	2017	2018	2019	2020	202	1 20	22 2	2023	2024	2025
Code	С		D	Е	F	G	Н			J	K	L	М
Month	ı	Jar	n Fel	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code)	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GS}	±20	V
Continuous Drain Current		Note 5)		1.9	
	1/ 101/	T _A =+70°C (Note 5)	I _D	1.5	٨
	$V_{GS} = 10V$	(Note 4)		1.5	Α
		(Note 7)		3.5	
Pulsed Drain Current (Note 6)			I _{DM}	8.6	А
Continuous Source Current (Body Diode) (Note 5)			I _S	2.5	Α
Pulsed Source Current (Body Diode) (Note 6)			I _{SM}	8.6	А

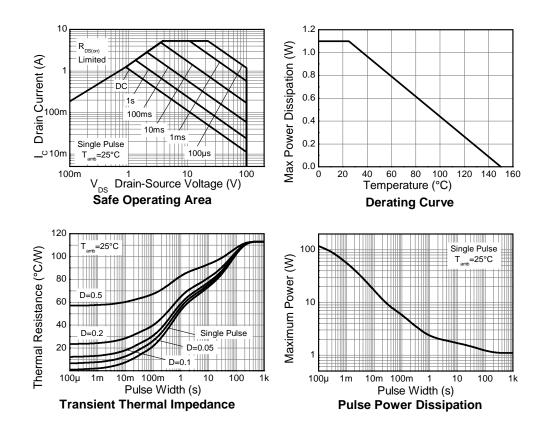
Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Note 4)		1.1		
Power Dissipation	(Note 5)	(Note 5) P _D		W	
	(Note 7)		6.3		
The arms of Decistance . It was time to Americant	(Note 4)	1	114	°C/W	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	73.5		
Thermal Resistance, Junction to Leads	$R_{ heta JL}$	19.7	°C/W		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

Notes:

- 4. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 5. For a device surface mounted on FR4 PCB measured at t ≤ 5 sec.
- 6. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.02, pulse width 300µs pulse width limited by maximum junction temperature.
- 7. Thermal resistance from junction to solder-point (at the end of the drain lead).

Thermal Characteristics





Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

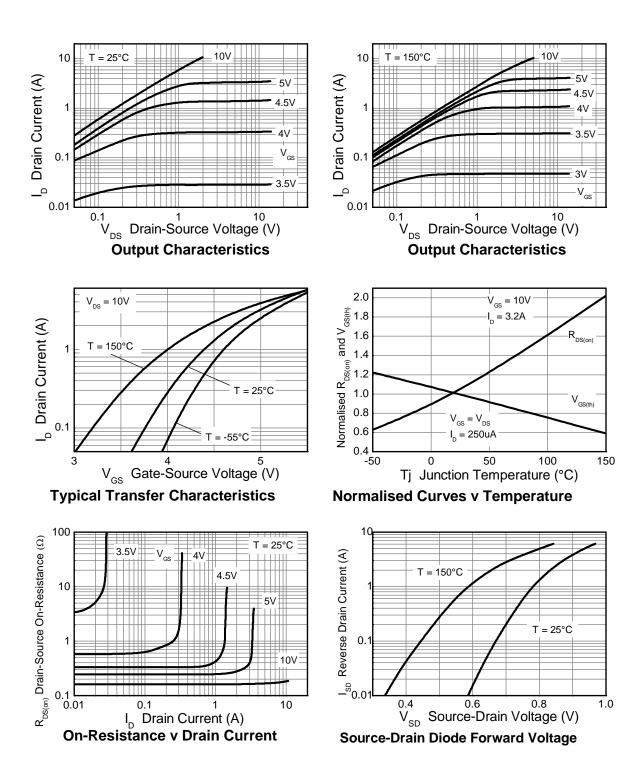
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	0.5	μА	$V_{DS} = 100V, V_{GS} = 0V$	
Gate-Source Leakage	Igss	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	2.0		4.0	V	$I_D = 250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 8)	P-a (a)			0.25	Ω	$V_{GS} = 10V, I_D = 3.2A$	
Static Drain-Source On-Nesistance (Note 6)	R _{DS (ON)}			0.30	32	$V_{GS} = 6V, I_D = 2.6A$	
Forward Transconductance (Notes 8 & 10)	g fs		5.0	_	S	$V_{DS} = 15V, I_D = 3.2A$	
Diode Forward Voltage (Note 8)	V_{SD}		0.87	0.95	V	$I_S = 3.2A, V_{GS} = 0V$	
Reverse Recovery Time (Note 10)	t _{rr}		27	_	ns	1 1 2 4 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	
Reverse Recovery Charge (Note 10)	Q _{rr}	_	32	_	nC	I _S = 1.2A, di/dt = 100A/μs	
DYNAMIC CHARACTERISTICS (Note 10)				•		•	
Input Capacitance	Ciss		405	_	pF	., 50,4,14, 0)4	
Output Capacitance	Coss		28.2	_	pF	$V_{DS} = 50V, V_{GS} = 0V$ -f = 1MHz	
Reverse Transfer Capacitance	Crss		14.2	_	pF	1 = 11/1112	
Gate Charge (Note 9)	Qg		4.2	_	nC	$V_{GS} = 5V, V_{DS} = 50V$ $I_D = 1.2A$	
Total Gate Charge (Note 9)	Qg	_	7.7	_	nC	10/1/	
Gate-Source Charge (Note 9)	Q_{gs}	_	1.8	_	nC	$V_{GS} = 10V, V_{DS} = 50V$	
Gate-Drain Charge (Note 9)	Q_{gd}	_	2.1	_	nC	$I_D = 1.2A$	
Turn-On Delay Time (Note 9)	t _{d(on)}	_	3.4	_	ns		
Turn-On Rise Time (Note 9)	t _r		2.2	_	ns	$V_{DD} = 30V, V_{GS} = 10V$	
Turn-Off Delay Time (Note 9)	t _{d(off)}	_	8	_	ns	$I_D = 1.2A, R_G \cong 6.0\Omega$	
Turn-Off Fall Time (Note 9)	t _f		3.2	_	ns	7	

Notes:

^{8.} Measured under pulsed conditions. Width ≤300µs. Duty cycle ≤2%.
9. Switching characteristics are independent of operating junction temperature.
10. For design aid only, not subject to production testing.

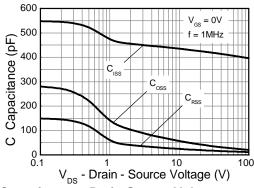


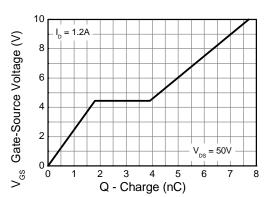
Typical Characteristics





Typical Characteristics (continued)

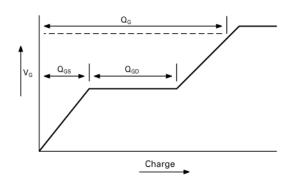




Capacitance v Drain-Source Voltage

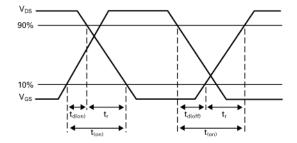
Gate-Source Voltage v Gate Charge

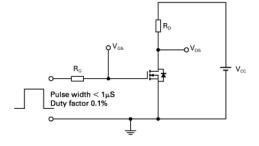
Test Circuits



Current regulator







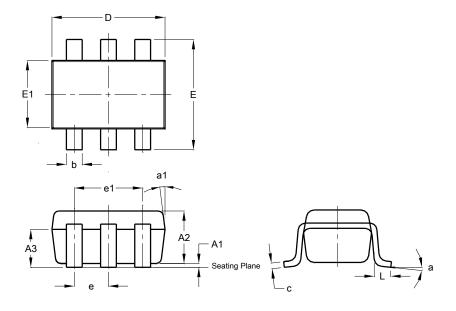
Switching time waveforms

Switching time test circuit



Package Outline Dimensions

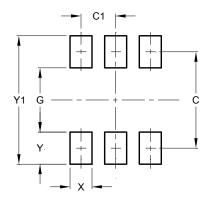
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26						
Dim	Min	Max	Тур				
A1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
А3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
С	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	-	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	-	7°				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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